#### Grant Agreement #?



# **Reconfigurable Microsystem Based on Wide Band** nanocom Gap Materials, Miniaturized and Nanostructured **RF-MEMS**

# Objectives

#### NANOCOM Missions

- Micro and Nano Technologies for smart systems:
  - GaN for power and robustness at high frequencies
  - Sensor for interfacing to real-world
  - MEMS and Mini-MEMS for reconfigurability and tunability
- NANOCOM Mission:
  - Integrate new nanostructured materials in MEMS technology to address charging effect and at the same time enhance thermal performances of the device

# **RT Developments**

Nanostructured materials integration

- Integration of nanostructured PZT Development and integration of single oriented
- carbon nanotubes in silicon nitride dielectric Development and first integration of diamond
- thin layers Dielectric electrical and thermal
- characterizations

### Development and fabrication of MiniMEMS



LCR	1560	100Pm ×150 22mm

## NANOCOM Objectives

- Developing innovative solutions for the RF front-end baseband by fabrication of agile RF transceiver and reconfigurable antennas with MEMS switches, sensors and actuators.
  - Objective 1: Achieve the integration of WBG devices and RF MEMS switches in LCP. Objective 2: Achieve the long-term reliability of RF-MEMS by solving poblems associated with these devices to bring this technology to industrial systems
  - Objective 3: Realize and optimise WBG based sensors and actuators and develop the necessary technology for their monolithic integration with WBG MMICs and RF MEMS.
  - Objective 4: Display the integration of all of these technologies through four demonstrators. •
  - Objective 5: After the fabrication of these demonstrators the fabrication process flow will be transfered by TRT to a foudry for industrialization.

#### Beyond state of the art MEMS performances

- Design and fabrication on GaN, Si and LTCC of MEMS and MiniMEMS switches, circuits and phase shifters
- Request:
- RF performance
- High power handling
- Thermal management
- Reliability
- Complementary SiP functions (passive functions, fluidic interfaces, etc)

Criteria	State of the art	NANOCOM goals
Frequency (GHz)	10 GHz	100MHz-20 GHz
Insertion loss (dB)	0.1 dB	0.1 dB
Isolation (dB)	35 dB	> 35 dB
Power handling (W)	40 dBm (10W)	> 45 dBm (30W)
Switching time	1 µs	0.1 µs

#### **III-Nitride based sensors**

- $\blacktriangleright$  GaN & AIN  $\rightarrow$  Gaz & T sensors
- Fab process compatible with MMIC & MEMS/NEMS process
- Gaz sensors
  - SAW sensor:
  - FBAR sensor:
  - Sensitivity of the FBAR based gas sensor: 2 (Hz/MHz)/(ng/cm2):
- Sensitivity of the SAW based gas sensor: 50-500 (Hz/ppm) (depending of coating material and gas species).
  - Integration into DEM #4

#### T sensor

- SAW monolithic with GaN MMIC (HEMT)
- T range from -40 to +120Þ Precision ~ 2-3 C

**Application Demonstrators** 

#### **DEM # 1**

- Reconfigurable smart active antennas with RF-MEMS switches
- X band, 20W peak

**DEM # 2** 

- RF-MEMS based agile radio (tunable filter) for air traffic mangement radars
- Wideband, high reliability

**DEM # 3** 

- RF-MEMS based reconfigurable reflect array antenna
- X band, 20W peak, short switching times (<500ns)

# **DEM # 4**

Miniaturized piezo sensor and actuator based on III-nitride materials



## T/R module for active antenna:

Replace circulators by RF-MEMS SPDTs integrated on the same substrate as the HPA and LNA



### Sensors an actuators:

Applications of wireless microsensor network with integrated sensor/actuator and microwave functions

# **Project Fact Sheet**



IOINT LINDERTAKING

- ENIAC Joint Undertaking SP 2 – Wireless communications
- SP 3 Energy efficiency
- Total cost: 3,3 M€ ENIAC Contribution: ? M€ National Contribution: ? M€ Total efforts: 626,25 pm
- 13 European Partners 5 countries 2 large industries 4 innovative SMEs 7 academic institutes
- Coordinator: Thales Research & Technology Fr
- Duration: 3 years

Palaiseau (91) - France

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